



P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^d	Q _g (Typ)	
- 60	0.060 at V _{GS} = - 10 V	- 19	26	
- 60	0.077 at V _{GS} = - 4.5 V	- 16.8	20	

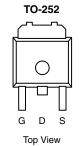
FEATURES

- Halogen-free According to IEC 61249-2-21 **Definition**
- TrenchFET® Power MOSFET
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC

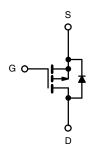


APPLICATIONS

- · High Side Switch for Full Bridge Converter
- · DC/DC Converter for LCD Display



Drain Connected to Tab



P-Channel MOSFET

Ordering Information:	SUD19P06-60-E3	(Lead (Pb)-free)

SUD19P06-60-GE3 (Lead (Pb)-free and Halogen free)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise note)					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	- 60		
Gate-Source Voltage		V_{GS}	± 20	- V	
Continuous Drain Current (T _{.I} = 150 °C)	T _C = 25 °C	I-	- 18.3		
Continuous Diain Current (1) = 150°C)	T _C = 125 °C	l _D	- 8.19	^	
Pulsed Drain Current		I _{DM}	- 30	A	
Avalanche Current, Single Pulse	L = 0.1 mH	I _{AS}	- 22		
Repetitive Avalanche Energy, Single Pulse ^a	L = 0.1 IIIIA	E _{AS}	24.2	mJ	
Dawar Dissination	T _C = 25 °C	P _D	38.5 ^c	W	
Power Dissipation	T _A = 25 °C	r D	2.3 ^{b, c}	l vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marian and Landing to Ambient	t ≤ 10 s	R_{thJA}	17	21	
Maximum Junction-to-Ambient ^b	Steady State	' 'thJA	45	55	°C/W
Maximum Junction-to-Case		R_{thJC}	2.7	3.25	

Notes:

- a. Duty cycle \leq 1 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Based up on $T_C = 25$ °C.

Document Number: 69253 S11-2132 Rev. B, 31-Oct-11



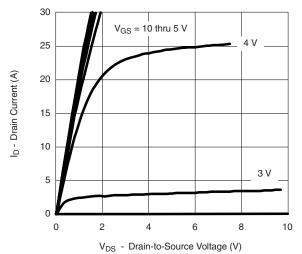
Parameter	Symbol	Test Conditions	Min .	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 60			V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
		V _{DS} = - 60 V, V _{GS} = 0 V			- 1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$			- 50	μΑ
		$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 150 ^{\circ} \text{ C}$			- 125	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 30			Α
		V _{GS} = - 10 V, I _D = - 10 A		0.048	0.060	Ω
Dunin Course On State Besistance	B	$V_{GS} = -10 \text{ V}, I_D = -10 \text{ A}, T_J = 125 \text{ °C}$			0.102	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 10 A, T _J = 150 °C			0.120	
		$V_{GS} = -4.5 \text{ V}, I_D = -5 \text{ A}$		0.061	0.077	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 10 A		22		S
Dynamic ^b						
Input Capacitance	C _{iss}			1140	1710	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$		130		pF
Reverse Transfer Capacitance	C _{rss}			90		
Total Gate Charge ^c	Qg			26	40	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -10 \text{ A}$		4.5		nC
Gate-Drain Charge ^c	Q _{gd}			7		
Gate Resistance	R _g	f = 1 MHz		7		Ω
Turn-On Delay Time ^c	t _{d(on)}			8	15	
Rise Time ^c	t _r	$V_{DD} = -30 \text{ V, R}_{L} = 3 \Omega$		9	15	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong -19 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 2.5 \Omega$		65	100	ns
Fall Time ^c	t _f	1		30	45	
Drain-Source Body Diode and Charact	eristics (T _C = 2	5 °C) ^b				
Continuous Current	I _S				- 30	
Pulsed Current	I _{SM}				- 30	Α
Forward Voltage ^a	V _{SD}	I _F = - 19 A, V _{GS} = 0 V		- 1	- 1.5	V
Reverse Recovery Time	t _{rr}	I _F = - 19 A, di/dt = 100 A/μs		41	61	ns

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

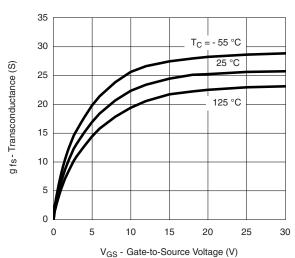
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



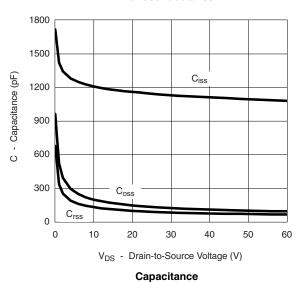
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

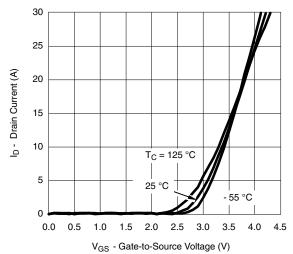


Output Characteristics

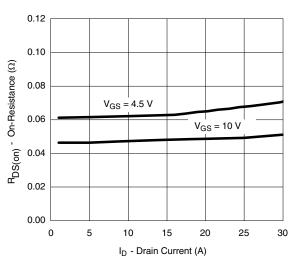


Transconductance

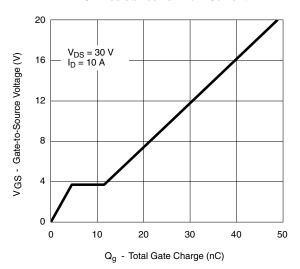




Transfer Characteristics

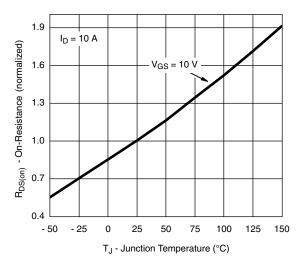


On-Resistance vs. Drain Current

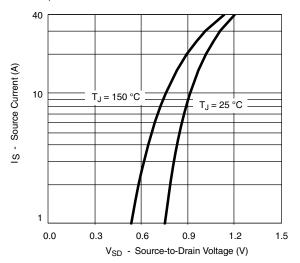


Gate Charge

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

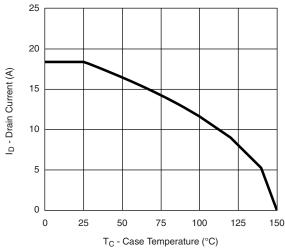


On-Resistance vs. Junction Temperature

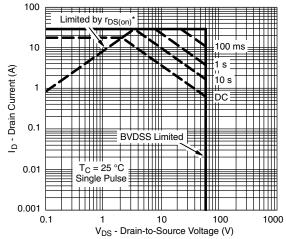


Source-Drain Diode Forward Voltage

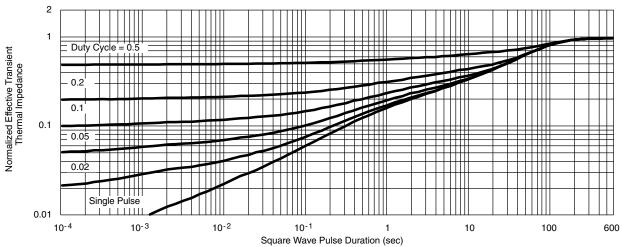
THERMAL RATINGS



Maximum Drain Current vs. Case Temperature



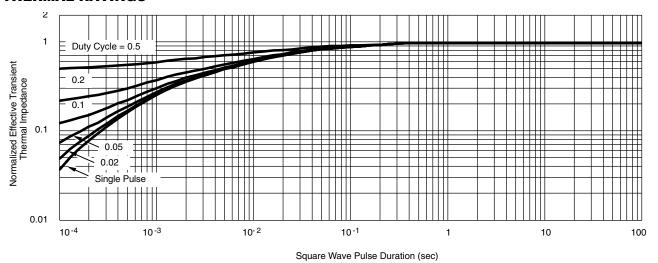
 * V_{GS} > minimum V_{GS} at which $r_{DS(on)}$ is specified Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS



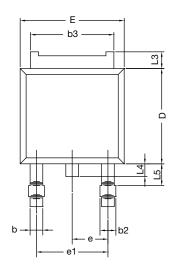
Normalized Thermal Transient Impedance, Junction-to-Case

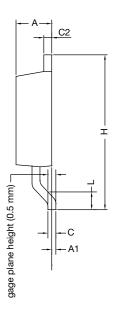
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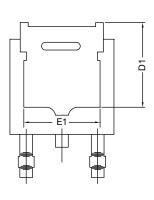


TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y







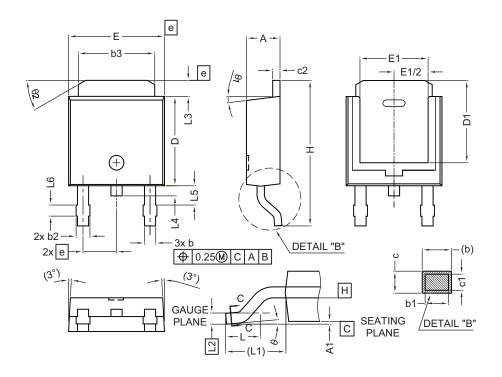
	MILLIMETERS		
DIM.	MIN.	MAX.	
А	2.18	2.38	
A1	-	0.127	
b	0.64	0.88	
b2	0.76	1.14	
b3	4.95	5.46	
С	0.46	0.61	
C2	0.46	0.89	
D	5.97	6.22	
D1	4.10	-	
Е	6.35	6.73	
E1	4.32	=	
Н	9.40	10.41	
е	2.28 BSC		
e1	4.56 BSC		
L	1.40	1.78	
L3	0.89	1.27	
L4	-	1.02	
L5	1.01	1.52	

Note

• Dimension L3 is for reference only



VERSION 2: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	2.18	2.39	
A1	-	0.13	
b	0.65	0.89	
b1	0.64	0.79	
b2	0.76	1.13	
b3	4.95	5.46	
С	0.46	0.61	
c1	0.41	0.56	
c2	0.46	0.60	
D	5.97	6.22	
D1	5.21	=	
Е	6.35	6.73	
E1	4.32	=	
е	2.29 BSC		
Н	9.94	10.34	

	MILLIMETERS		
DIM.	MIN.	MAX.	
L	1.50	1.78	
L1	2.74	ref.	
L2	0.51	BSC	
L3	0.89	1.27	
L4	-	1.02	
L5	1.14	1.49	
L6	0.65	0.85	
θ	0°	10°	
θ1	0°	15°	
θ2	25°	35°	

Notes

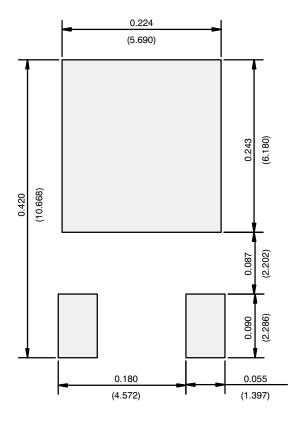
- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- · Radius on terminal is optional

ECN: E19-0649-Rev. Q, 16-Dec-2019

DWG: 5347



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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